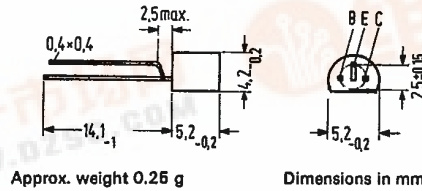


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**PNP Silicon Planar Transistor** **BF 926**  
 SIEMENS AKTIENGESELLSCHAFT 04554 D

BF 926 is an epitaxial PNP silicon planar transistor in TO 92 plastic package (10 A 3 DIN 41868). The transistor is intended for use in VHF oscillator stages, in particular for driving MOS mixer stages.

Type	Ordering code
BF 926	Q62702-F 678



**Maximum ratings**

Collector-emitter voltage	$-V_{CEO}$	30	V
Collector-base voltage	$-V_{CBO}$	40	V
Emitter-base voltage	$-V_{EBO}$	4	V
Collector current	$-I_C$	25	mA
Emitter current	$-I_E$	30	mA
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55 to +150	°C
Total power dissipation ( $T_{amb} = 45^\circ\text{C}$ )	$P_{tot}$	300	mW

**Thermal resistance**

Junction to ambient air	$R_{thJA}$	<350	K/W
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**Static characteristics** ( $T_{amb} = 25^{\circ}\text{C}$ )

Collector cutoff current ( $-V_{CB} = 20\text{ V}$ )	$-I_{CBO}$	<60	nA
Collector-emitter breakdown voltage ( $-I_C = 2\text{ mA}$ )	$-V_{CEO}$	>30	V
Collector-base breakdown voltage ( $-I_C = 10\ \mu\text{A}$ )	$-V_{CBO}$	>40	V
Emitter-base breakdown voltage ( $-I_E = 10\ \mu\text{A}$ )	$-V_{EBO}$	>4	V
DC current gain ( $-I_C = 1\text{ mA}$ ; $-V_{CE} = 10\text{ V}$ )	$h_{FE}$	80 (>30)	-

**Dynamic characteristics** ( $T_{amb} = 25^{\circ}\text{C}$ )

Transition frequency ( $-I_C = 5\text{ mA}$ ; $-V_{CE} = 10\text{ V}$ ; $f = 100\text{ MHz}$ )	$f_T$	600	MHz
Reverse transfer capacitance ( $-V_{CB} = 10\text{ V}$ ; $-I_C = 5\text{ mA}$ ; $f = 1\text{ MHz}$ )	$-C_{12e}$	0.6	pF
Output capacitance ( $-I_E = 0$ ; $-V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$ )	$C_{OB}$	0.8	pF
Input capacitance ( $-V_{EBO} = 0.15\text{ V}$ ; $NF = 1\text{ MHz}$ )	$C_{EBO}$	2	pF